

Docket: CS 99 - 065  
S/N: 09/442,499



COPY OF PAPER  
ORIGINALLY FILED

1105

To: Commissioner of Patents and Trademarks  
Washington, D.C. 20231

From: George O. Saile, Reg. No. 19,572  
20 McIntosh Drive  
Poughkeepsie, N.Y. 12603

Subject:

RECEIVED  
MAR 06 2002  
TC 1700

Serial No.: 09/442,499 Filed: 11/18/99  
Inventor: Ho

Title: Plasma Etch Method For Forming Plasma Etched Silicon  
Layer

Group Art Unit: 1763 Examiner: Goudreau, G.  
Attorney Docket: CS 99 - 065

H/C  
3/18/02  
MW

#### RESPONSE TO PATENT OFFICE ACTION

Dear Sir:

In response to the office action dated 11/07/01, please consider the  
following remarks:

#### CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with the  
United States Postal Service as first class mail in an envelope addressed to:  
Commissioner of Patent and Trademarks, Washington, D.C. 20231, on  
February 1, 2002.

Signature/Date

  
2/1/02  
Stephen B. Ackerman, Reg #37,761